

BC556B, BC557, A, B, C, BC558B, C



ON Semiconductor™

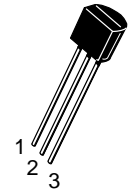
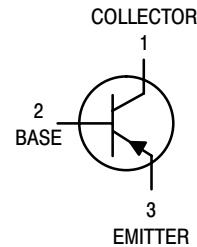
<http://onsemi.com>

Amplifier Transistors

PNP Silicon

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}		Vdc
	BC556	-65	
	BC557	-45	
	BC558	-30	
Collector-Base Voltage	V_{CBO}		Vdc
	BC556	-80	
	BC557	-50	
	BC558	-30	
Emitter-Base Voltage	V_{EBO}	-5.0	Vdc
Collector Current – Continuous – Peak	I_C	-100	mAdc
	I_{CM}	-200	
Base Current – Peak	I_{BM}	-200	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625	mW
		5.0	mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5	Watts
		12	mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$



CASE 29
TO-92
STYLE 17

ORDERING INFORMATION

Device	Package	Shipping
BC556B	TO-92	5000 Units/Box
BC556BRL1	TO-92	2000/Tape & Reel
BC556BZL1	TO-92	2000/Ammo Pack
BC557	TO-92	5000 Units/Box
BC557ZL1	TO-92	2000/Ammo Pack
BC557A	TO-92	5000 Units/Box
BC557AZL1	TO-92	2000/Ammo Pack
BC557B	TO-92	5000 Units/Box
BC557BRL1	TO-92	2000/Tape & Reel
BC557BZL1	TO-92	2000/Ammo Pack
BC557C	TO-92	5000 Units/Box
BC557CZL1	TO-92	2000/Ammo Pack
BC558B	TO-92	5000 Units/Box
BC558BRL	TO-92	2000/Tape & Reel
BC558BRL1	TO-92	2000/Tape & Reel
BC558BZL1	TO-92	2000/Ammo Pack
BC558C	TO-92	5000 Units/Box
BC558CRL1	TO-92	2000/Tape & Reel
BC558ZL1	TO-92	2000/Ammo Pack
BC558CZL1	TO-92	2000/Ammo Pack

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	$^\circ\text{C/W}$

BC556B, BC557, A, B, C, BC558B, C

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector–Emitter Breakdown Voltage ($I_C = -2.0\text{ mA}$, $I_B = 0$)	BC556	$V_{(BR)CEO}$	-65	-	-	V
	BC557		-45	-	-	
	BC558		-30	-	-	
Collector–Base Breakdown Voltage ($I_C = -100\ \mu\text{A}$)	BC556	$V_{(BR)CBO}$	-80	-	-	V
	BC557		-50	-	-	
	BC558		-30	-	-	
Emitter–Base Breakdown Voltage ($I_E = -100\ \mu\text{A}$, $I_C = 0$)	BC556	$V_{(BR)EBO}$	-5.0	-	-	V
	BC557		-5.0	-	-	
	BC558		-5.0	-	-	
Collector–Emitter Leakage Current ($V_{CES} = -40\text{ V}$) ($V_{CES} = -20\text{ V}$) ($V_{CES} = -20\text{ V}$, $T_A = 125^\circ\text{C}$)	BC556	I_{CES}	-	-2.0	-100	nA
	BC557		-	-2.0	-100	
	BC558		-	-2.0	-100	
	BC556		-	-	-4.0	μA
	BC557		-	-	-4.0	
	BC558		-	-	-4.0	

BC556B, BC557, A, B, C, BC558B, C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit	
ON CHARACTERISTICS						
DC Current Gain (I _C = -10 μAdc, V _{CE} = -5.0 V)	h _{FE}	A Series Device	-	90	-	-
		B Series Devices	-	150	-	
		C Series Devices	-	270	-	
(I _C = -2.0 mAdc, V _{CE} = -5.0 V)	BC557	BC557	120	-	800	
		A Series Device	120	170	220	
		B Series Devices	180	290	460	
	C Series Devices	420	500	800		
(I _C = -100 mAdc, V _{CE} = -5.0 V)	A Series Device	A Series Device	-	120	-	
		B Series Devices	-	180	-	
		C Series Devices	-	300	-	
Collector-Emitter Saturation Voltage (I _C = -10 mAdc, I _B = -0.5 mAdc)	V _{CE(sat)}	(I _C = -10 mAdc, I _B = see Note 1)	-	-0.075	-0.3	V
		(I _C = -100 mAdc, I _B = -5.0 mAdc)	-	-0.25	-0.65	
			-	-0.3	-0.6	
Base-Emitter Saturation Voltage (I _C = -10 mAdc, I _B = -0.5 mAdc)	V _{BE(sat)}	(I _C = -100 mAdc, I _B = -5.0 mAdc)	-	-0.7	-	V
			-	-1.0	-	
Base-Emitter On Voltage (I _C = -2.0 mAdc, V _{CE} = -5.0 Vdc)	V _{BE(on)}	(I _C = -10 mAdc, V _{CE} = -5.0 Vdc)	-0.55	-0.62	-0.7	V
			-	-0.7	-0.82	

SMALL-SIGNAL CHARACTERISTICS

Current-Gain – Bandwidth Product (I _C = -10 mA, V _{CE} = -5.0 V, f = 100 MHz)	BC556 BC557 BC558	f _T	-	280 320 360	-	MHz
Output Capacitance (V _{CB} = -10 V, I _C = 0, f = 1.0 MHz)		C _{ob}	-	3.0	6.0	pF
Noise Figure (I _C = -0.2 mAdc, V _{CE} = -5.0 V, R _S = 2.0 kΩ, f = 1.0 kHz, Δf = 200 Hz)	BC556 BC557 BC558	NF	-	2.0 2.0 2.0	10 10 10	dB
Small-Signal Current Gain (I _C = -2.0 mAdc, V _{CE} = 5.0 V, f = 1.0 kHz)	BC557 A Series Device B Series Devices C Series Devices	h _{fe}	125 125 240 450	- - - -	900 260 500 900	-

Note 1: I_C = -10 mAdc on the constant base current characteristics, which yields the point I_C = -11 mAdc, V_{CE} = -1.0 V.

BC556B, BC557, A, B, C, BC558B, C

BC557/BC558

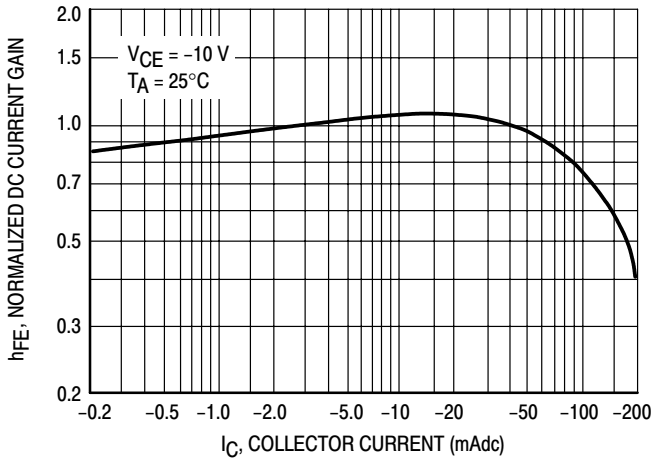


Figure 1. Normalized DC Current Gain

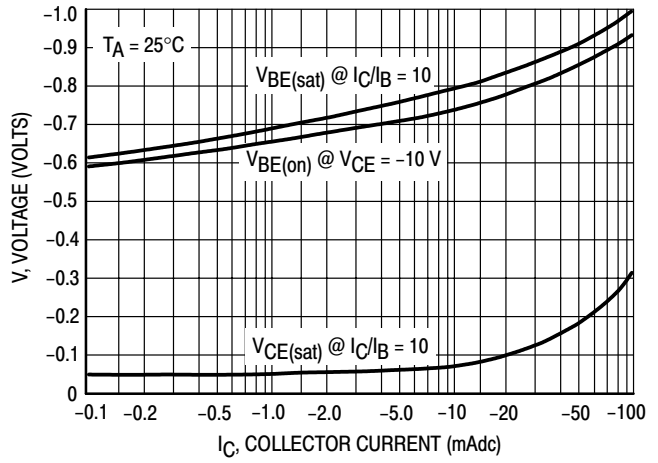


Figure 2. "Saturation" and "On" Voltages

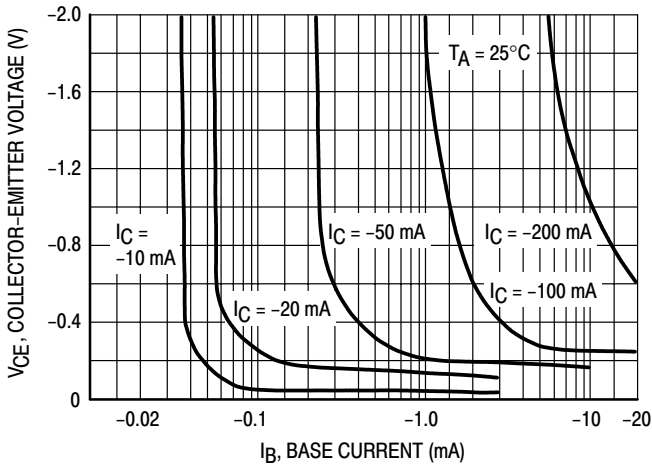


Figure 3. Collector Saturation Region

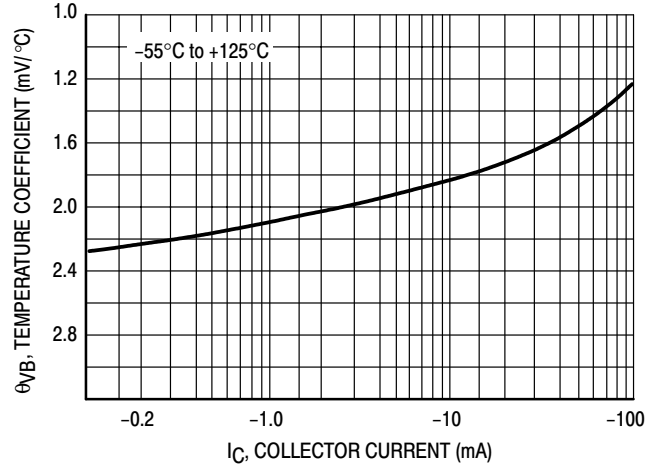


Figure 4. Base-Emitter Temperature Coefficient

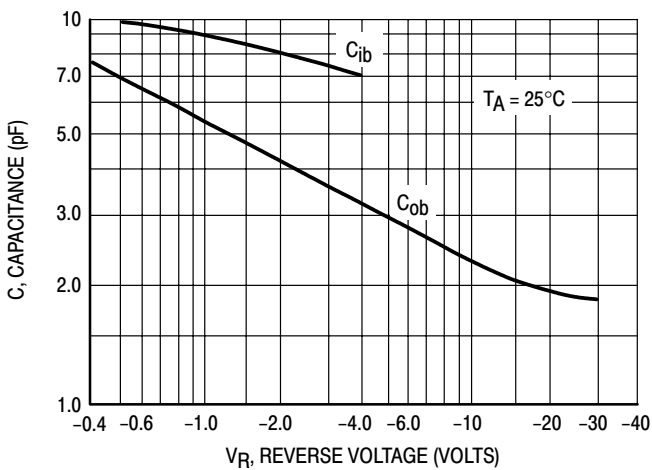


Figure 5. Capacitances

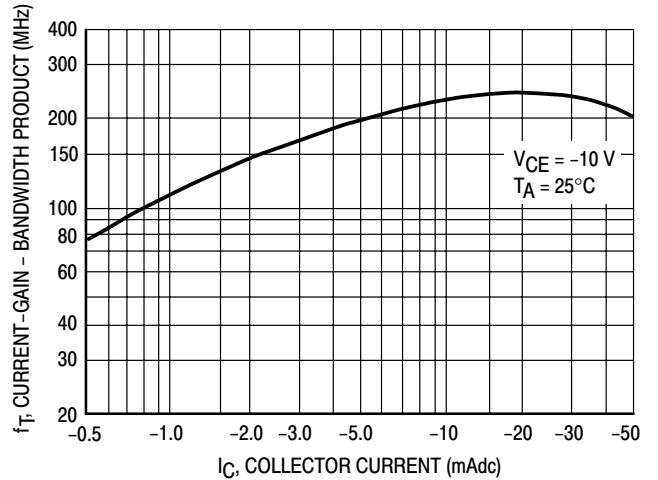


Figure 6. Current-Gain - Bandwidth Product

BC556B, BC557, A, B, C, BC558B, C

BC556

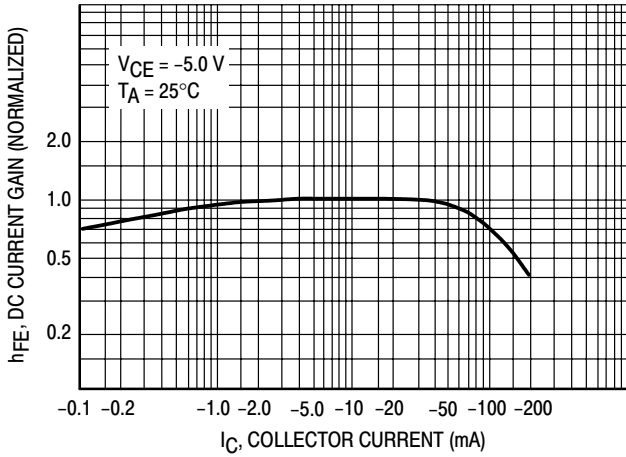


Figure 7. DC Current Gain

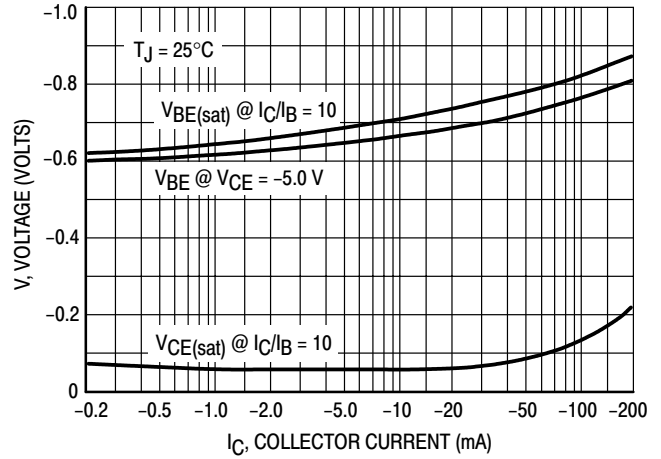


Figure 8. "On" Voltage

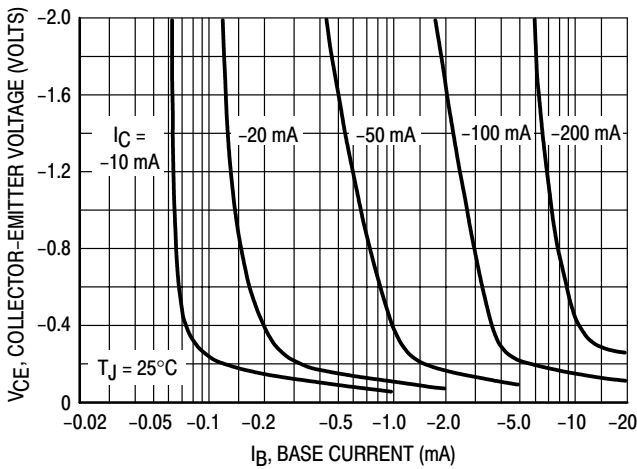


Figure 9. Collector Saturation Region

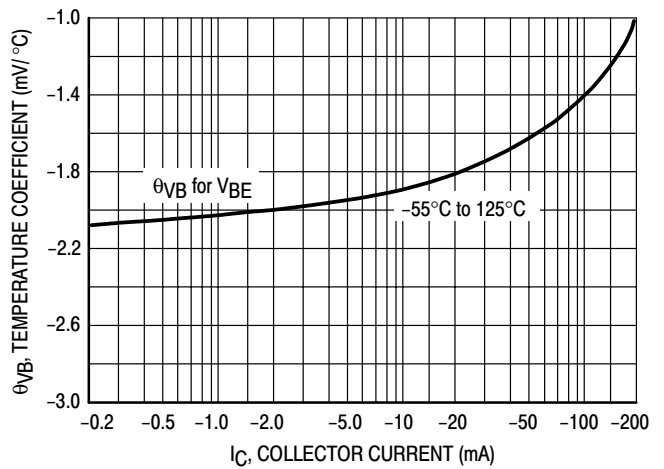


Figure 10. Base-Emitter Temperature Coefficient

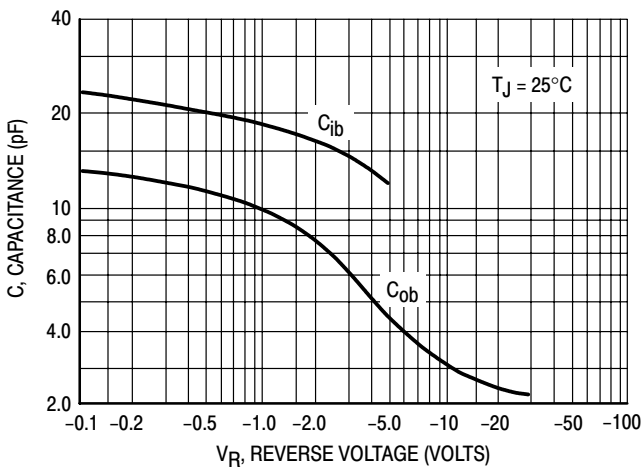


Figure 11. Capacitance

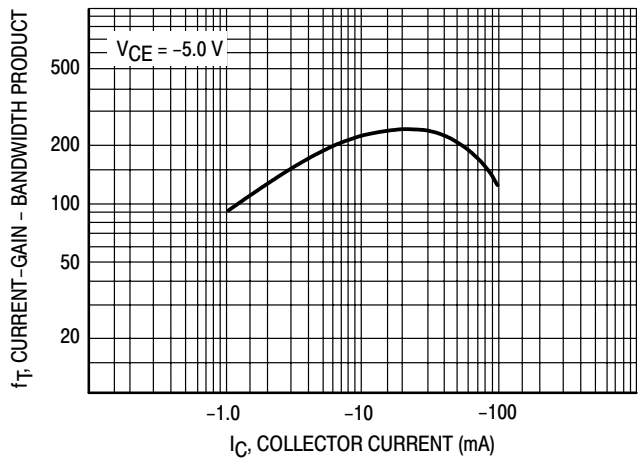


Figure 12. Current-Gain - Bandwidth Product

BC556B, BC557, A, B, C, BC558B, C

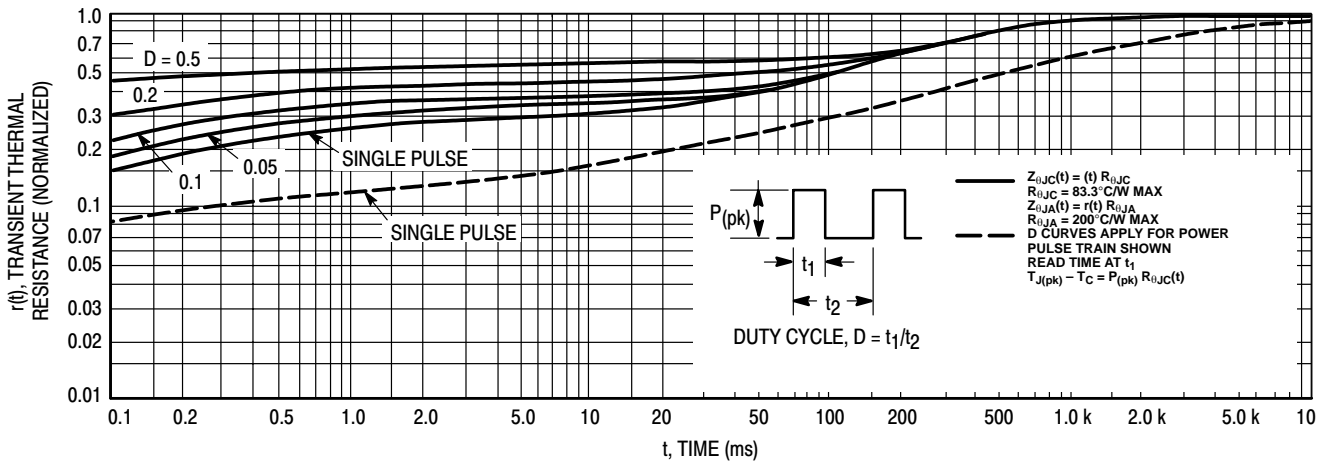


Figure 13. Thermal Response

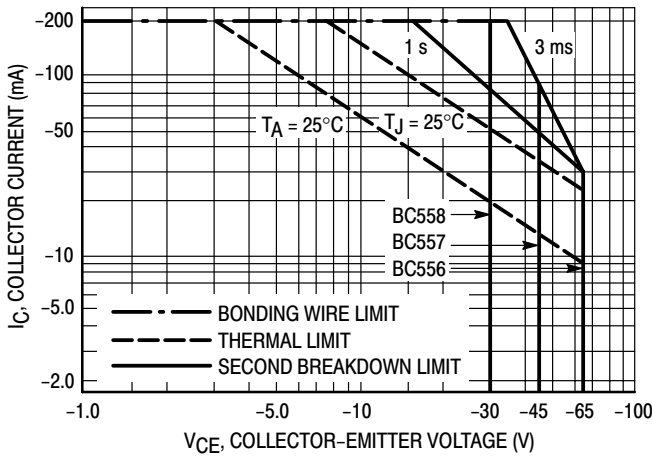


Figure 14. Active Region – Safe Operating Area

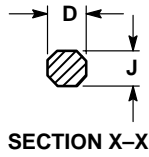
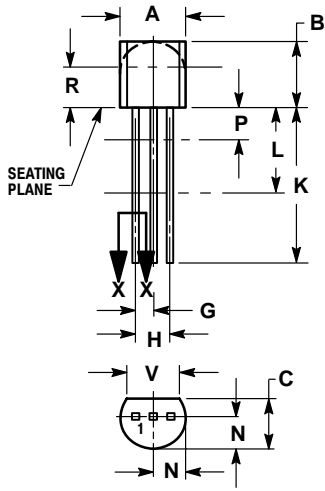
The safe operating area curves indicate I_C - V_{CE} limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 14 is based upon $T_{J(pk)} = 150^\circ\text{C}$; T_C or T_A is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^\circ\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 13. At high case or ambient temperatures, thermal limitations will reduce the power than can be handled to values less than the limitations imposed by second breakdown.

BC556B, BC557, A, B, C, BC558B, C

PACKAGE DIMENSIONS

TO-92
(TO-226)
CASE 29-11
ISSUE AL



NOTES:


1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---

STYLE 17:

1. COLLECTOR
2. BASE
3. EMITTER

BC556B, BC557, A, B, C, BC558B, C

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

PUBLICATION ORDERING INFORMATION

Literature Fulfillment:

Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: ONlit@hibbertco.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

JAPAN: ON Semiconductor, Japan Customer Focus Center
4-32-1 Nishi-Gotanda, Shinagawa-ku, Tokyo, Japan 141-0031
Phone: 81-3-5740-2700
Email: r14525@onsemi.com

ON Semiconductor Website: <http://onsemi.com>

For additional information, please contact your local Sales Representative.